

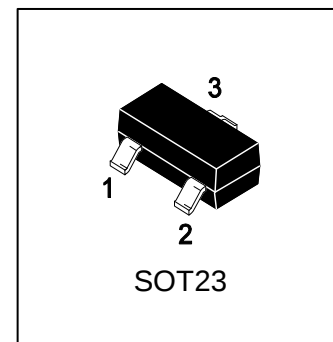
L2SC2412KRLT1G

S-L2SC2412KRLT1G

General Purpose Transistors NPN Silicon

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

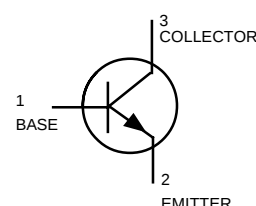


2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L2SC2412KRLT1G	BR	3000/Tape&Reel
L2SC2412KRLT3G	BR	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

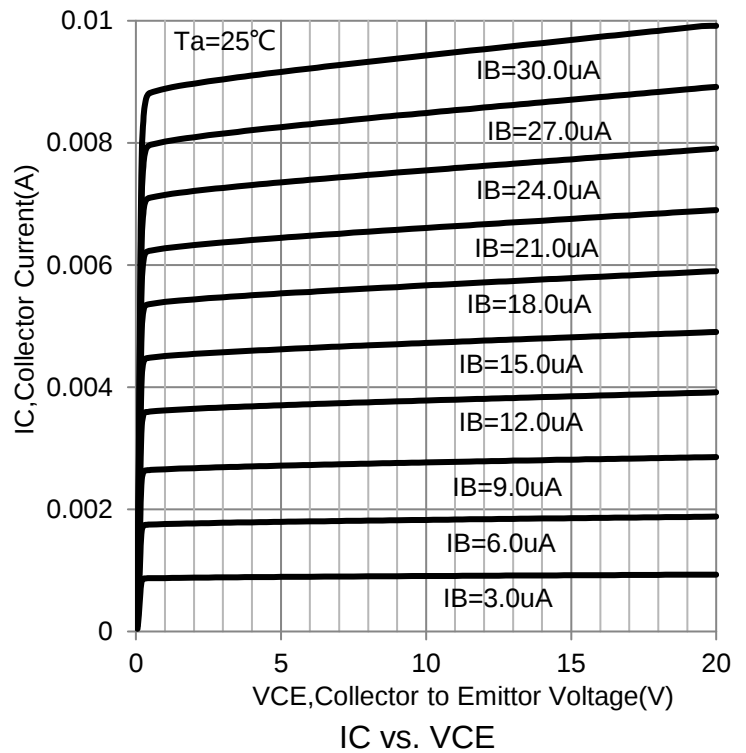
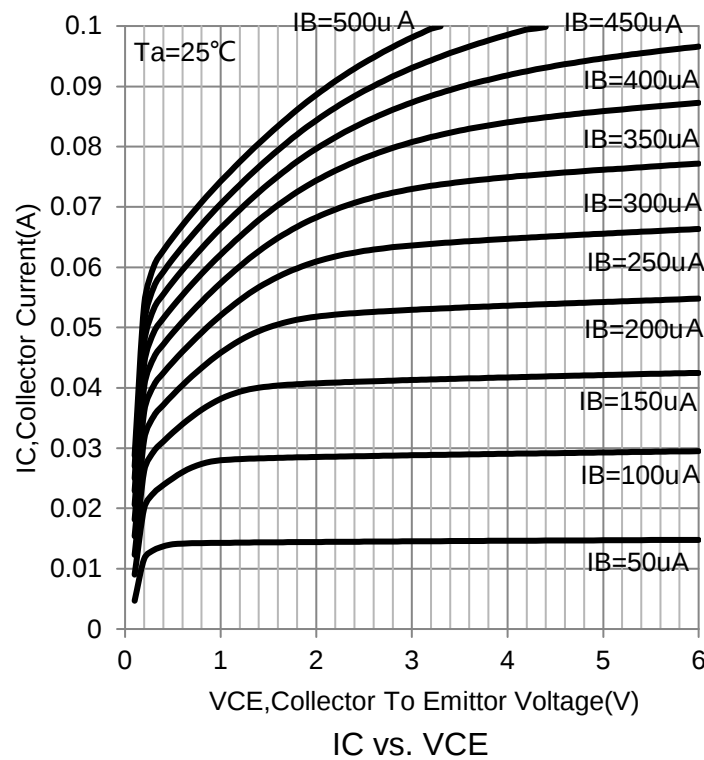
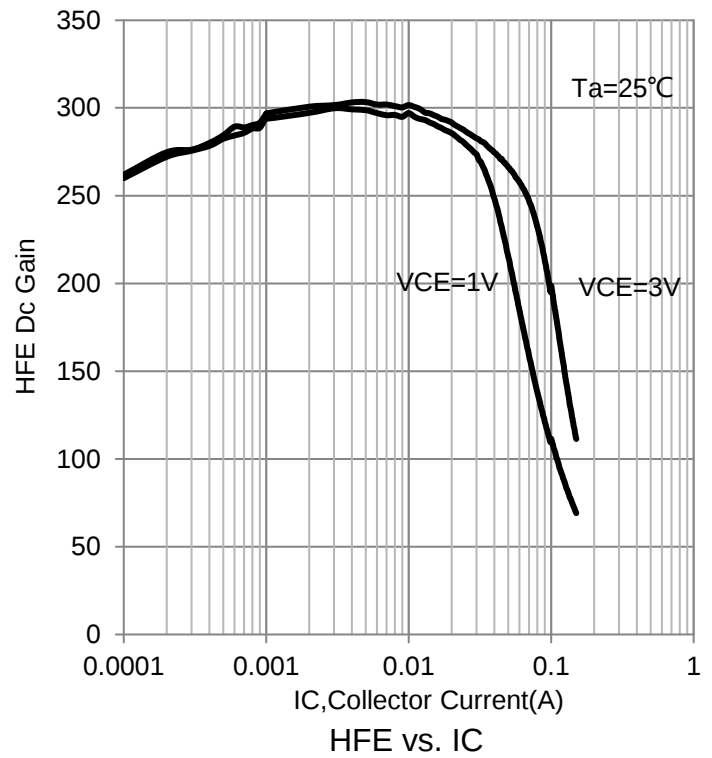
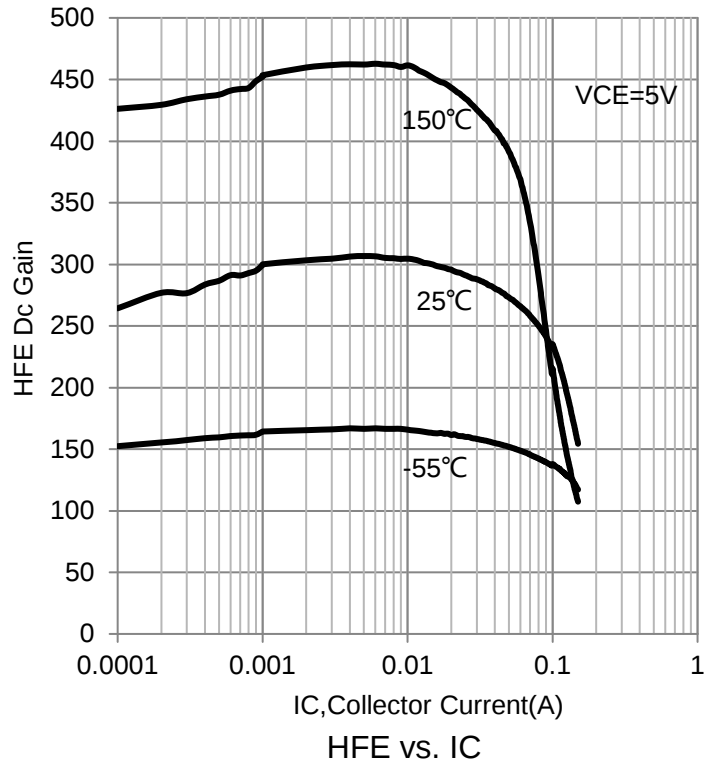
Parameter	Symbol	Limits	Unit
Collector-Emitter Voltage	V _{CEO}	50	V
Collector-Base voltage	V _{CBO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Collector current —Continuous	I _C	150	mA
Collector power dissipation	P _C	225	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

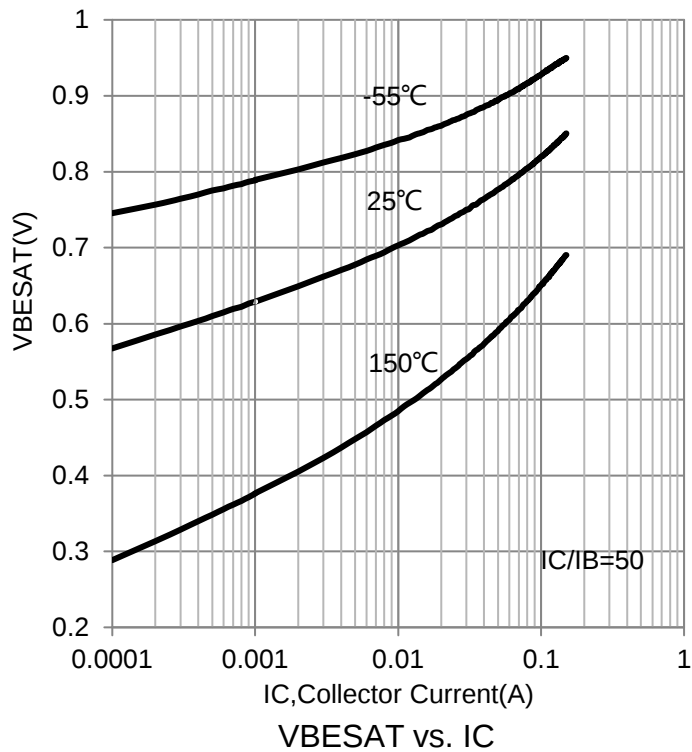
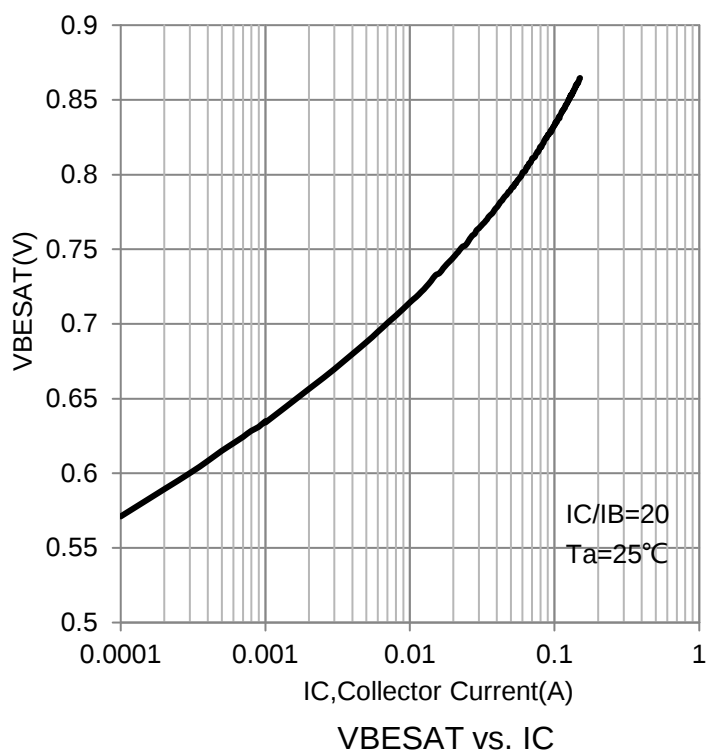
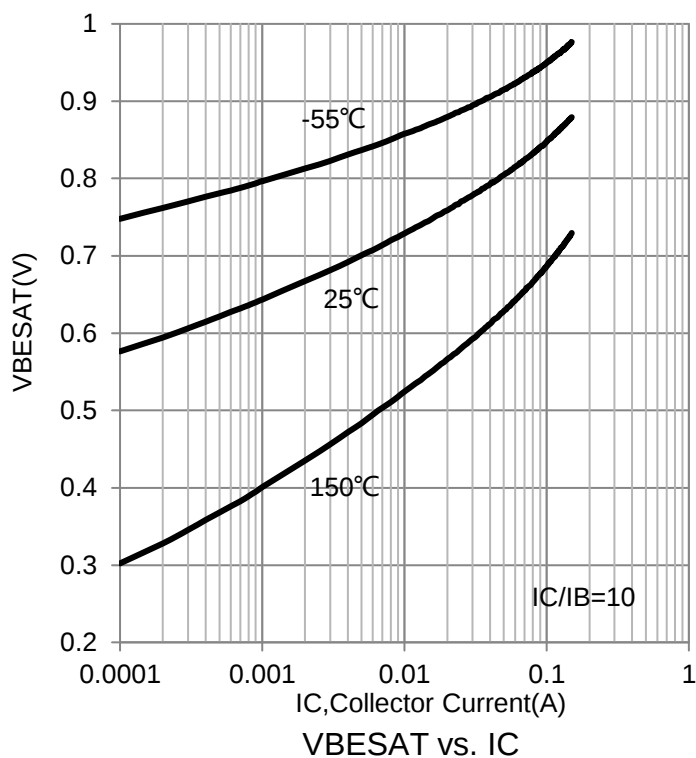
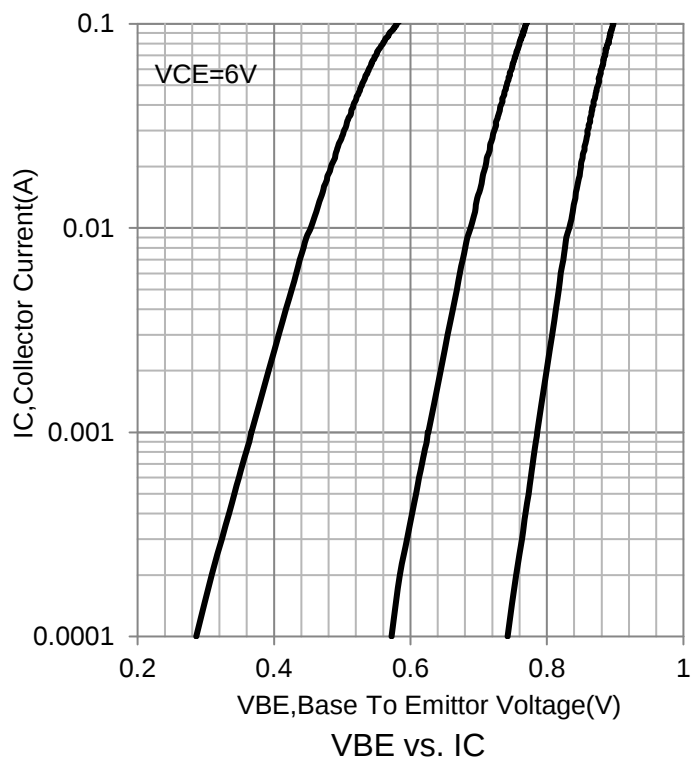


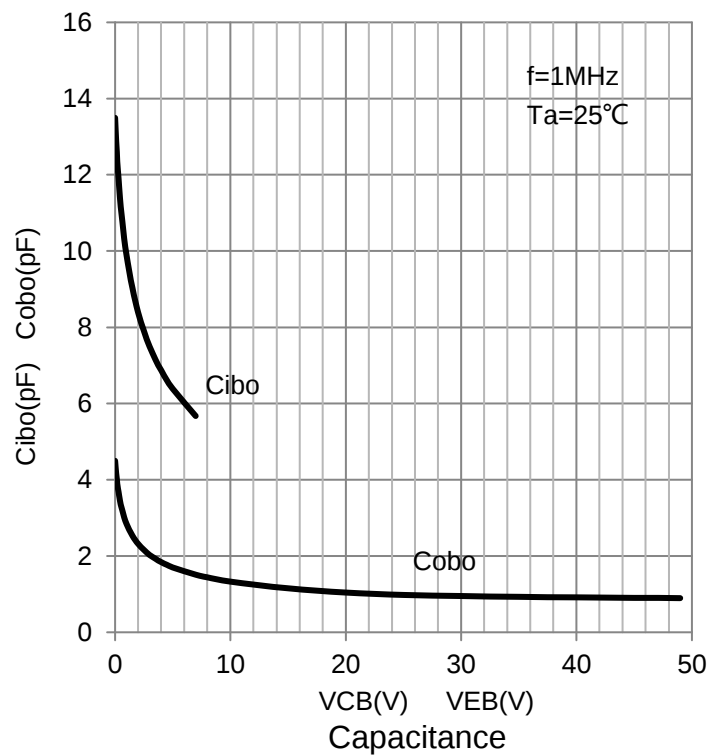
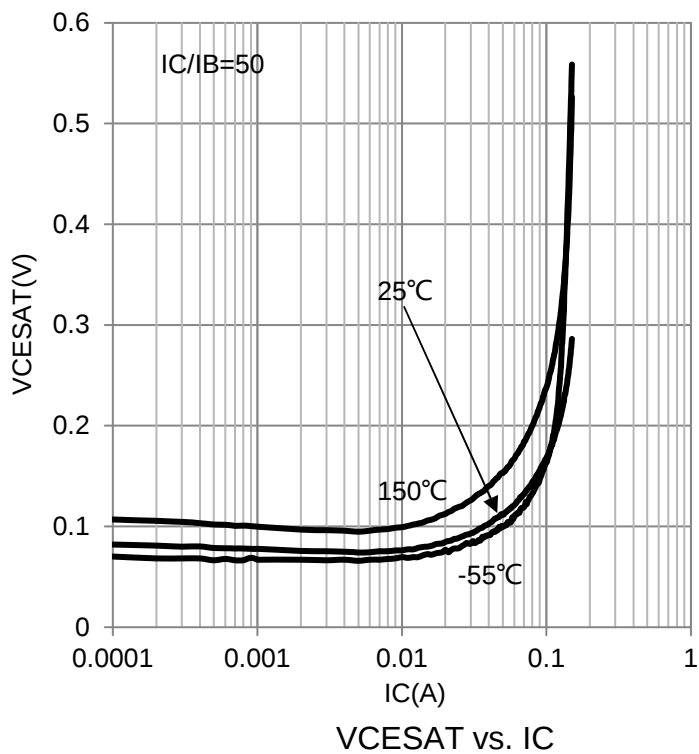
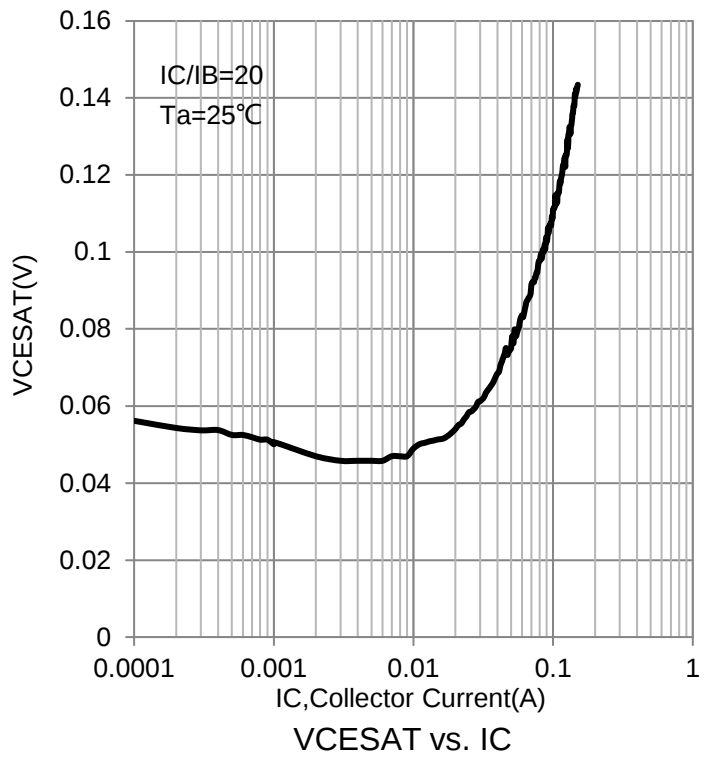
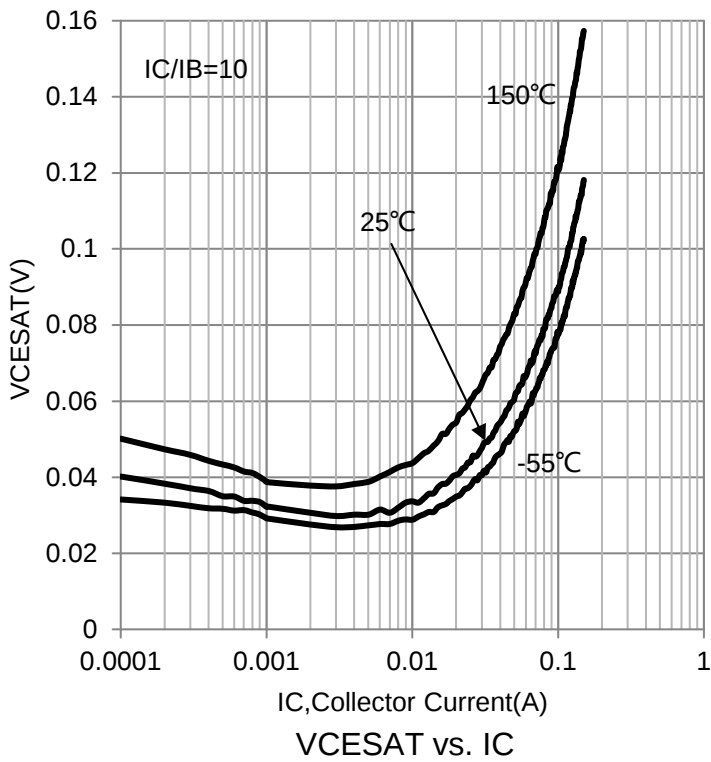
4. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage (I _C = 1.0mA)	V _{(BR)CEO}	50	-	-	V
Emitter-Base Breakdown Voltage (I _E = 50μA)	V _{(BR)EBO}	7	-	-	V
Collector-Base Breakdown voltage (I _C = 50μA)	V _{(BR)CBO}	60	-	-	V
Collector Cutoff Current (V _{CB} = 60 V)	I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current (V _{EB} = 7V)	I _{EBO}	-	-	0.1	μA
Collector-Emitter Saturation Voltage (I _C / I _B = 50 mA / 5mA)	V _{CE(S)}	-	-	0.4	V
DC current transfer ratio (V _{CE} = 6 V, I _C = 1mA)	h _{FE}	180	-	390	
Transition frequency (V _{CE} = 12 V, I _E = 2mA, f = 30MHz)	f _T	-	180	-	MHz
Output capacitance (V _{CB} = 12 V, I _E = 0A, f = 1MHz)	C _{ob}	-	2	3.5	pF

5.ELECTRICAL CHARACTERISTICS CURVES



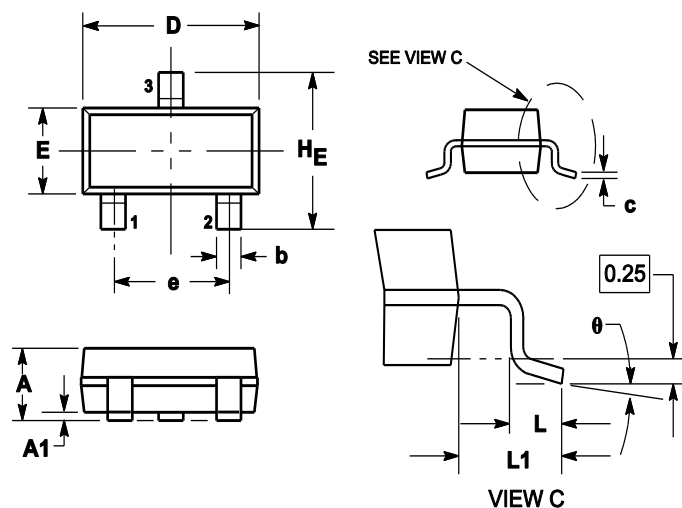
5.ELECTRICAL CHARACTERISTICS CURVES(Con.)


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6.OUTLINE AND DIMENSIONS

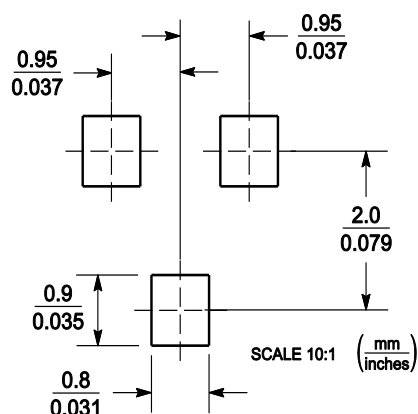
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H _E	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

7.SOLDERING FOOTPRINT



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)